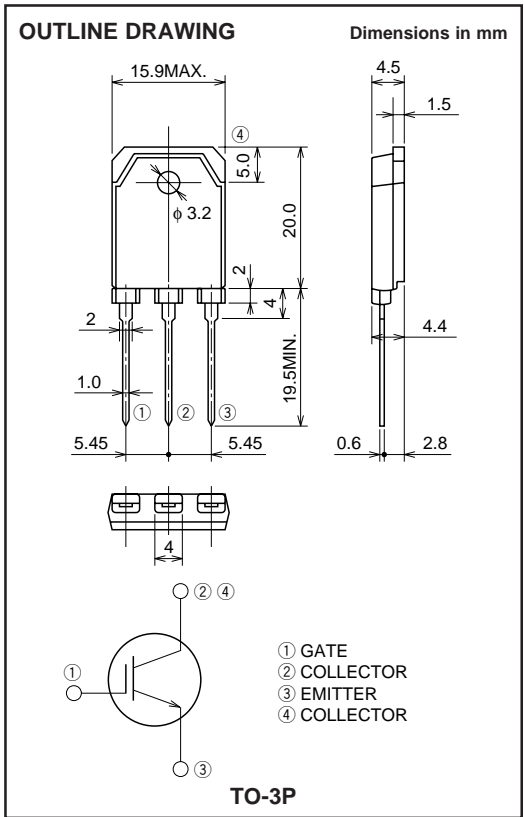
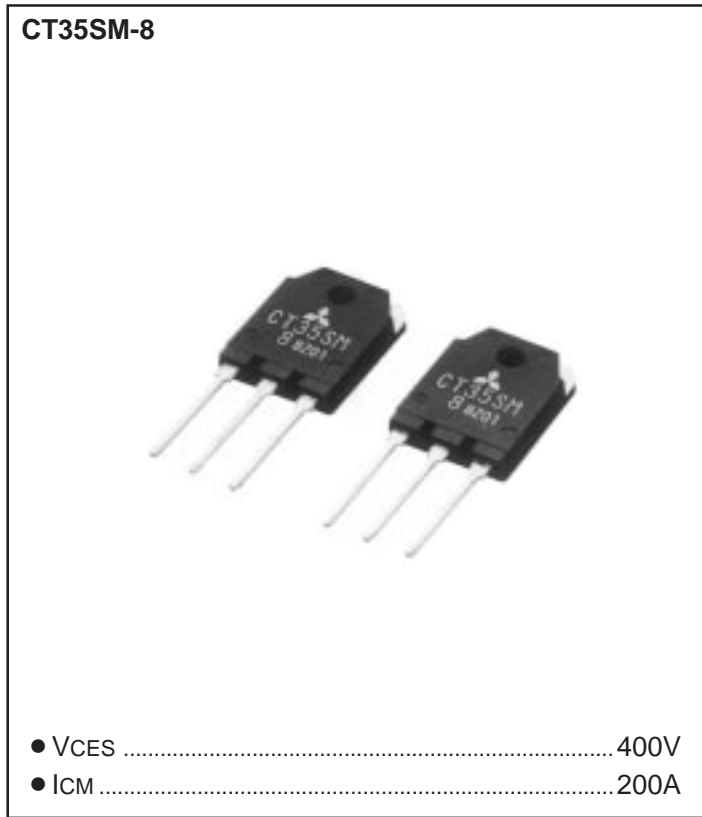


MITSUBISHI INSULATED GATE BIPOLAR TRANSISTOR

CT35SM-8

STROBE FLASHER USE



APPLICATION
Strobe Flasher.

MAXIMUM RATINGS (Tc = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
V _{CE} S	Collector-emitter voltage	V _{GE} = 0V	400	V
V _{GE} S	Gate-emitter voltage	V _{CE} = 0V, See notice 4	±30	V
V _{GEM}	Peak gate-emitter voltage	V _{CE} = 0V, t _w = 0.5s	±40	V
I _{CM}	Collector current (Pulsed)	See figure 1	200	A
T _j	Junction temperature		-40 ~ +150	°C
T _{stg}	Storage temperature		-40 ~ +150	°C

ELECTRICAL CHARACTERISTICS (T_j = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V(BR)CES	Collector-emitter breakdown voltage	I _C = 1mA, V _{GE} = 0V	450	—	—	V
I _{CE} S	Collector-emitter leakage current	V _{CE} = 400V, V _{GE} = 0V	—	—	10	μA
I _{GE} S	Gate-emitter leakage current	V _{GE} = ±40V, V _{CE} = 0V	—	—	±0.1	μA
V _{GE(th)}	Gate-emitter threshold voltage	V _{CE} = 10V, I _C = 1mA	—	—	7.0	V

PERFORMANCE CURVES

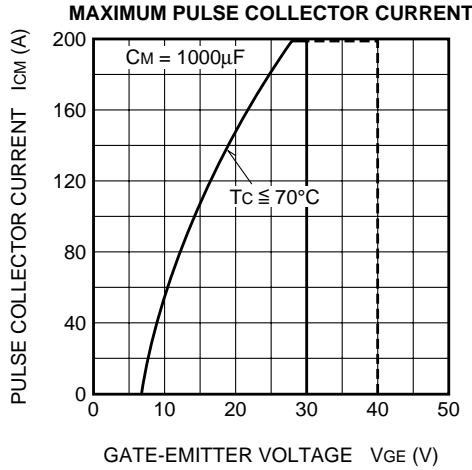


Figure 1

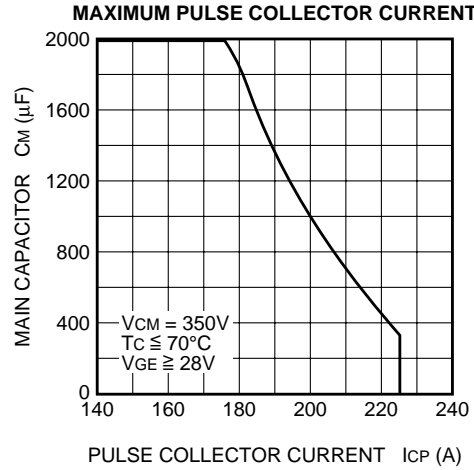
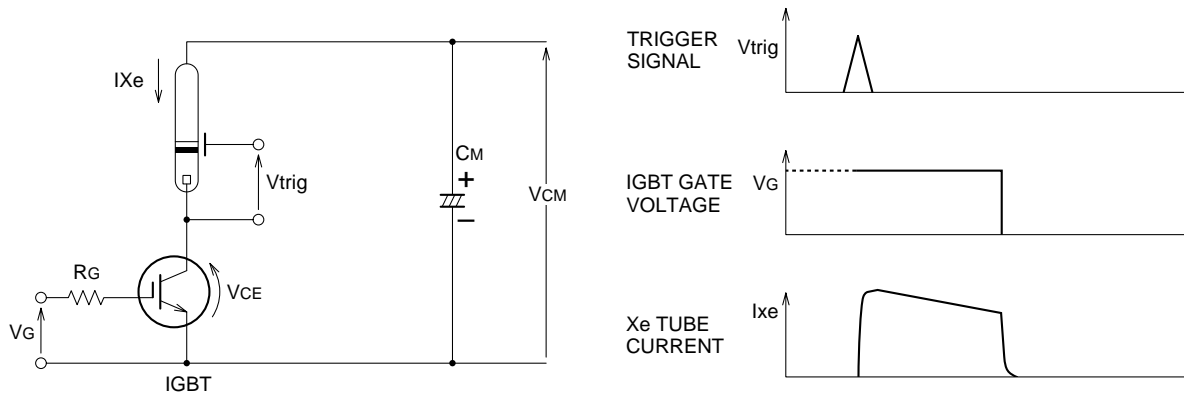


Figure 2

APPLICATION EXAMPLE



RECOMMEND CONDITION	MAXIMUM CONDITION
V _{CM} = 330V	360V
I _P = 180A	200A
C _M = 800μF	1000μF
V _{GE} = 28V	

- Notice 1. Gate drive voltage during on-period must be applied to satisfy the rating of maximum pulse collector current. And reverse gate current during turn-off must be kept less than 1A. (In general, it is satisfied if R_G ≥ 30Ω)
- Notice 2. IGBT has MOS structure and its gate is insulated by thin silicon oxide. So please handle carefully not to suffer from electrostatic charge.
- Notice 3. The operation life should be endured 5,000 shots under the charge current (I_{xe} ≤ 200A : full luminescence condition) of main condenser (C_M=1000μF). Repetition period under full luminescence condition is over 3 seconds.
- Notice 4. Total operation hours must be applied within 5,000 hours.